

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A silicon wafer having a front surface, a back surface, a circumferential edge portion and a region between the front and back surfaces, the silicon wafer comprising:

a first denuded zone being formed up to a predetermined distance from the front surface;

a second denuded zone being formed up to a predetermined distance from the back surface; and

a bulk region being formed between the first and second denuded zones,

wherein a concentration profile of defects in the bulk region has a distribution which is maintained substantially constant in a direction from the front surface to the back surface, said defects being bulk micro-defects (BMD) including oxygen precipitates and bulk stacking faults.

2. (Canceled)

3. (Original) A silicon wafer according to claim 2, wherein the concentration of the defects in the region between the first and the second denuded zones has a distribution which is maintained constant in a range from about 3.0×10^8 ea/cm³ to about 1.0×10^{10} ea/cm³.

4. (Currently Amended) A silicon wafer having a front surface, a back surface, a circumferential edge portion and a region between the front and back surfaces, the silicon wafer comprising:

a first denuded zone being formed up to a predetermined distance from the front surface;

a second denuded zone being formed up to a predetermined distance from the back surface; and,

a bulk region being formed between the first and second denuded zones,

wherein a concentration profile of defects in the bulk region has a distribution which is maintained substantially constant in a direction from the front surface to the back surface; and

wherein the defects are bulk stacking faults.

5. (Original) A silicon wafer according to claim 4, wherein the concentration of the defects in the region between the first and the second denuded zones has a distribution which is maintained constant in a range from about 1.0×10^8 ea/cm³ to about 3.0×10^9 ea/cm³.

6. (Original) A silicon wafer according to claim 1, wherein the distances of the first and the second denuded zones from the front and back surfaces respectively are in a range from about 5 μ m to about 40 μ m.

7. (Original) A silicon wafer according to claim 1, wherein the first and the second denuded zones are substantially defectless regions in which oxygen precipitates and bulk stacking faults are substantially removed.

8. (Currently Amended) A silicon wafer having a front surface, a back surface, a circumferential edge portion and a region between the front and back surfaces, wherein the region between the front and back surfaces comprises:

a first denuded zone being formed up to a predetermined distance from the front surface;

a second denuded zone being formed up to a predetermined distance from the back surface; and

a bulk region being formed between the first and second denuded zones,

wherein a concentration profile of defects between the front and back surfaces of the wafer has a stepwise shape having an axial symmetry at the center between the front and back surfaces of the wafer,

wherein the bulk region has vertically-rising concentration gradients at boundaries of the first and second denuded zones and a horizontal concentration gradient over the bulk region, and

wherein a concentration profile of defects in the bulk region has a planar shape within a range of variation of about 10% or less, said defects being bulk micro-defects (BMD) including oxygen precipitates and bulk stacking faults.

9. (Canceled)

10. (Original) A silicon wafer according to claim 9, wherein the concentration of the defects in the region between the first and the second denuded zones has a distribution which is maintained constant in a range from about 3.0×10^8 ea/cm³ to about 1.0×10^{10} ea/cm³.

11. (Currently Amended) A silicon wafer having a front surface, a back surface, a circumferential edge portion and a region between the front and back surfaces, wherein the region between the front and back surfaces comprises:

a first denuded zone being formed up to a predetermined distance from the front surface;

a second denuded zone being formed up to a predetermined distance from the back surface; and

a bulk region being formed between the first and second denuded zones,

wherein a concentration profile of defects between the front and back surfaces of the wafer has a stepwise shape having an axial symmetry at the center between the front and back surfaces of the wafer,

wherein the bulk region has vertically-rising concentration gradients at boundaries of the first and second denuded zones and a horizontal concentration gradient over the bulk region,

wherein a concentration profile of defects in the bulk region has a planar shape within a range of variation of about 10% or less, and

wherein the defects are bulk stacking faults.

12. (Original) A silicon wafer according to claim 11, wherein the concentration of the defects in the region between the first and the second denuded zones has a distribution which is maintained constant in a range from about 1.0×10^8 ea/cm³ to 3.0×10^9 ea/cm³.

13. (Original) A silicon wafer according to claim 8, wherein the distances of the first and the second denuded zones from the front and back edges respectively are in a range from about 5 μ m to about 40 μ m.

14. - 46 (Canceled)